




# 100V N-Channel SGT MOSFET

<p><b>General Description</b></p> <ul style="list-style-type: none"> <li>● Trench Power SGT technology</li> <li>● Very low on-resistance <math>R_{DS(ON)}</math></li> <li>● Low Gate Charge</li> <li>● Excellent Gate Charge x <math>R_{DS(ON)}</math> Product</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>● High Frequency Switching and Synchronous Rectification</li> </ul>	<p><b>Product Summary</b></p> <table border="0"> <tr> <td><math>V_{DS}</math></td> <td>100V</td> </tr> <tr> <td><math>I_D</math> (at <math>V_{GS}=10V</math>)</td> <td>55A</td> </tr> <tr> <td><math>R_{DS(ON)}</math> (at <math>V_{GS}=10V</math>)</td> <td>&lt; 12m<math>\Omega</math></td> </tr> <tr> <td><math>R_{DS(ON)}</math> (at <math>V_{GS}=4.5V</math>)</td> <td>&lt; 15m<math>\Omega</math></td> </tr> </table> <p>100% UIS Tested 100% DVDS Tested</p> 	$V_{DS}$	100V	$I_D$ (at $V_{GS}=10V$ )	55A	$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 12m $\Omega$	$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	< 15m $\Omega$
$V_{DS}$	100V								
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$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	< 15m $\Omega$								



Part Number	Package Type	Form	Marking
TSD120N10AT	TO-252	Tape&Reel	TSD120N10AT
TSP120N10AT	TO-220	Tube	TSP120N10AT
TSG120N10AT	DFN5x6	Tape&Reel	TSG120N10AT

**Absolute Maximum Ratings ( $T_A = 25^\circ C$  unless otherwise noted)**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>B</sup>	$I_D$	$T_C = 25^\circ C$	55
		$T_C = 100^\circ C$	39
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	220	A
Avalanche Current <sup>A</sup>	$I_{AS}$	20	A
Single Pulse Avalanche Energy <sup>A</sup>	$E_{AS}$	60	mJ
Power Dissipation <sup>C</sup>	$P_D$	$T_C = 25^\circ C$	83.3
		$T_C = 100^\circ C$	41.7
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 175	$^\circ C$

**Thermal Characteristics**

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Case	$R_{\theta JC}$	1.8	$^\circ C/W$
Maximum Junction-to-Ambient	$R_{\theta JA}$	50	



Electrical Characteristics( $T_J = 25^\circ\text{C}$ unless otherwise noted)						
Symbol	Parameter	Conditions	Value			Units
			Min	Typ	Max	
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 100\text{V}, V_{GS} = 0\text{V}$	$T_J = 25^\circ\text{C}$		1	$\mu\text{A}$
			$T_J = 125^\circ\text{C}$		100	
$I_{GSS}$	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.1	1.6	2.4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{V}, I_D = 30\text{A}$		10	12	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 30\text{A}$		12	15	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		32		S
$V_{SD}$	Diode Forward Voltage	$I_S = 30\text{A}, V_{GS} = 0\text{V}$			1	V
$I_S$	Maximum Body-Diode Continuous Current <sup>B</sup>				55	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 50\text{V}, f = 1\text{MHz}$		1766		$\text{pF}$
$C_{oss}$	Output Capacitance			201		
$C_{rss}$	Reverse Transfer Capacitance			4.1		
$R_g$	Gate Resistance	$f = 1\text{MHz}$		2.3		$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS} = 10\text{V}, V_{DS} = 50\text{V}, I_D = 20\text{A}$		25.7		nC
$Q_g(4.5\text{V})$	Gate Source Charge			13		
$Q_{gs}$	Gate Source Charge			4.3		
$Q_{gd}$	Gate Drain Charge			5.3		
$Q_{oss}$	Output Charge	$V_{GS} = 0\text{V}, V_{DS} = 50\text{V}$		34.2		
$t_{D(on)}$	Turn-On Delay Time	$V_{GS} = 10\text{V}, V_{DS} = 50\text{V}, I_D = 20\text{A}, R_G = 1.8\Omega$		33		ns
$t_r$	Turn-On Rise Time			4		
$t_{D(off)}$	Turn-Off Delay Time			55		
$t_f$	Turn-Off Fall Time			3.1		
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F = 20\text{A}, di/dt = 100\text{A}/\mu\text{s}$		49		ns
$Q_{rr}$	Body Diode Reverse Recovery Charge			71		nC

A. Single pulse width limited by maximum junction temperature.

B. The maximum current rating is package limited.

C. The power dissipation  $P_D$  is based on  $T_{J(MAX)} = 175^\circ\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.



### TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

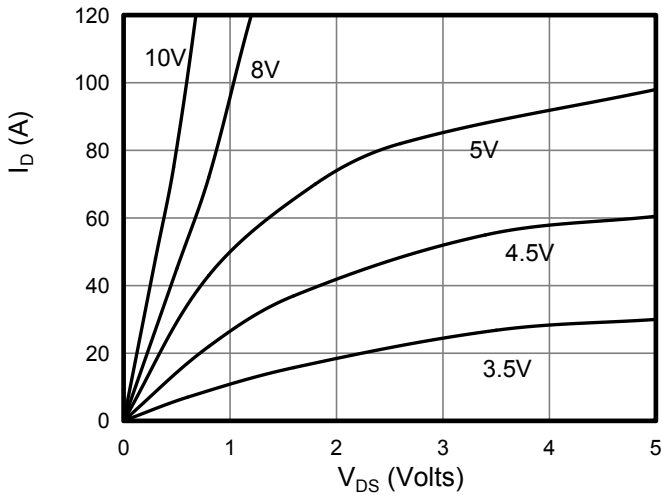


Figure 1: On-Region Characteristics

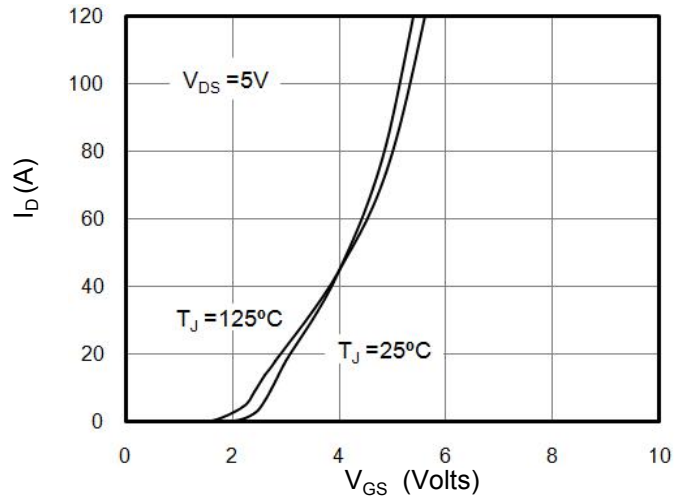


Figure 2: Transfer Characteristics

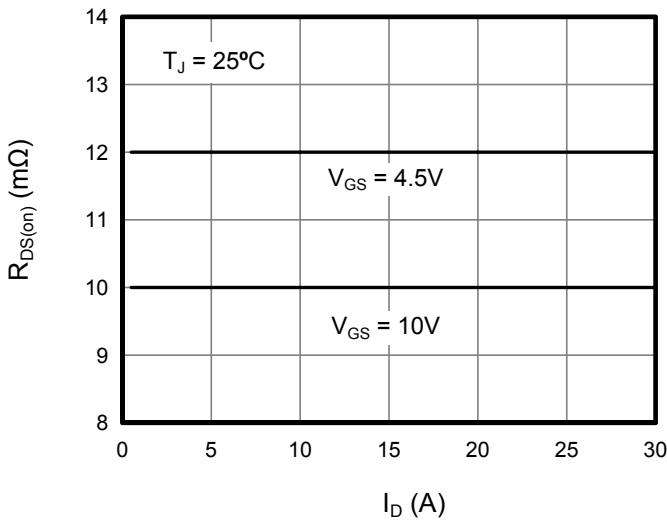


Figure 3: On-Resistance vs. Drain Current

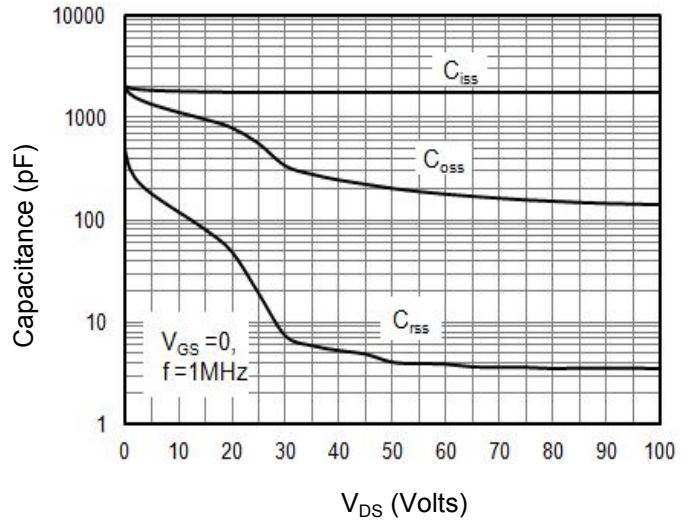


Figure 4: Capacitance Characteristics

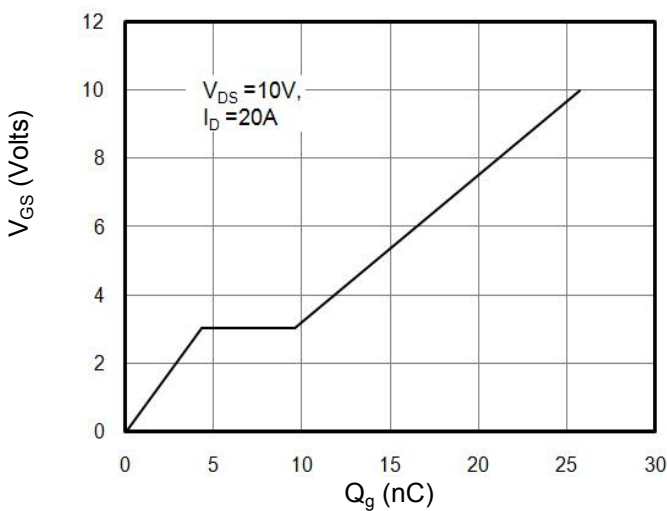


Figure 5: Gate Charge Characteristics

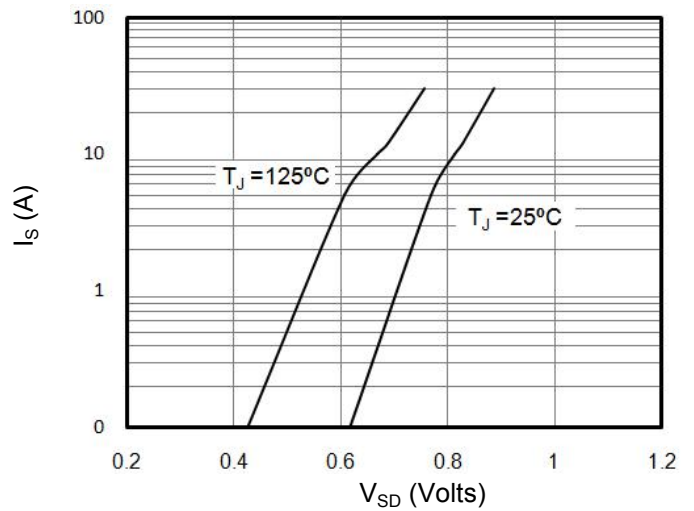


Figure 6: Body Diode Forward Voltage



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

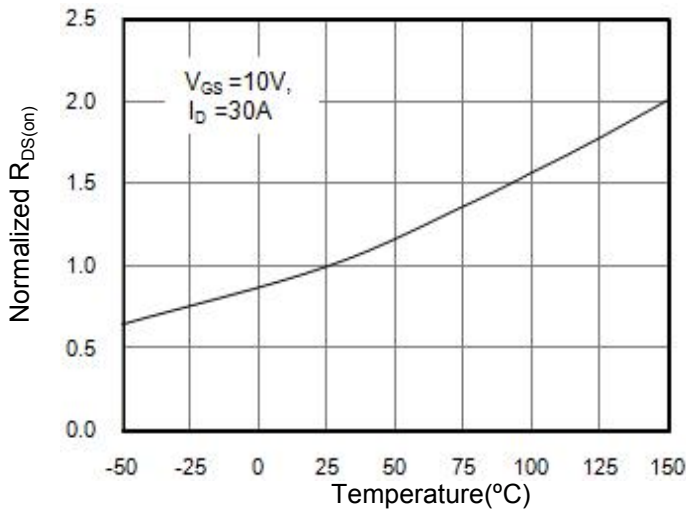


Figure 7: On-Resistance vs. Junction Temperature

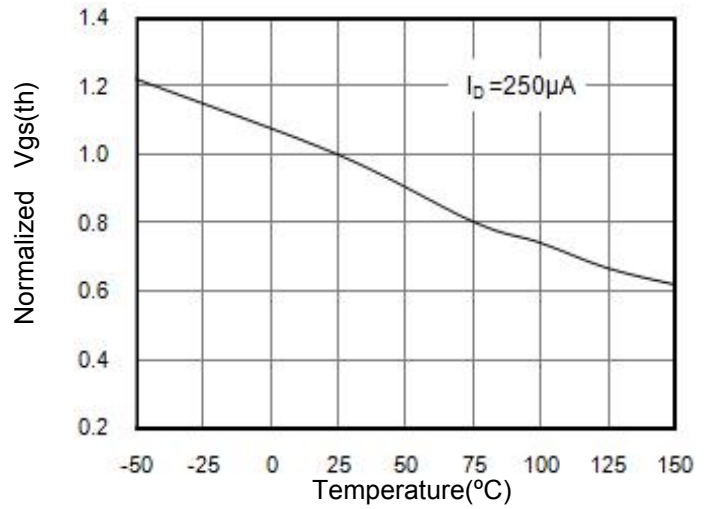


Figure 8:  $V_{GS(th)}$  vs. Junction Temperature

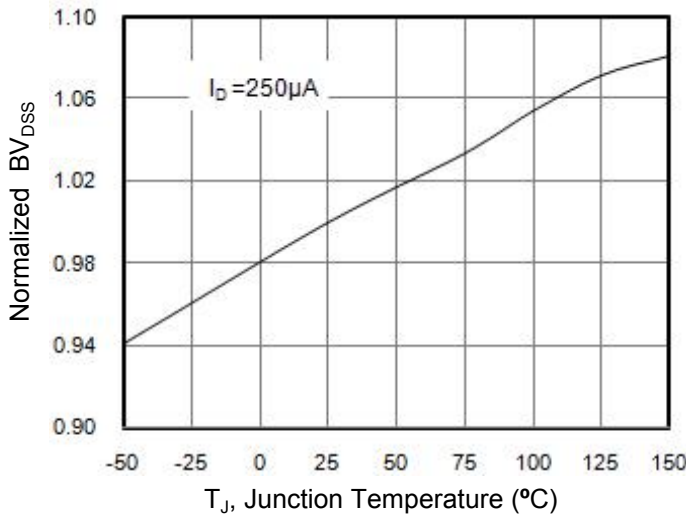


Figure 9:  $BV_{DS}$  vs. Junction Temperature

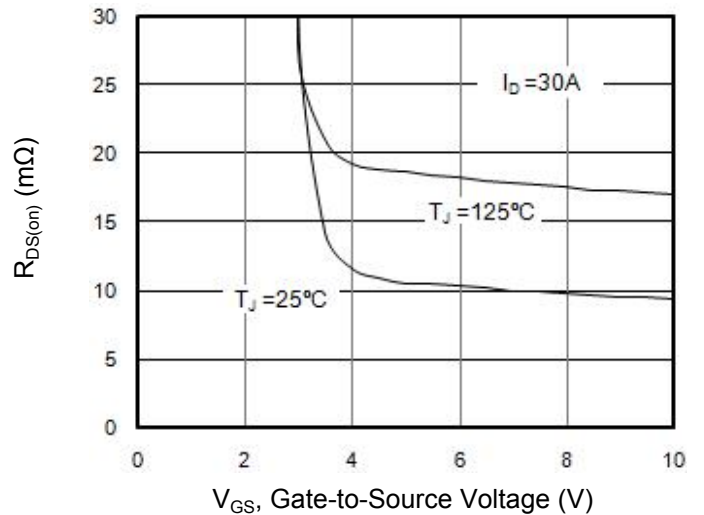


Figure 10: On-Resistance vs. Gate-Source Voltage

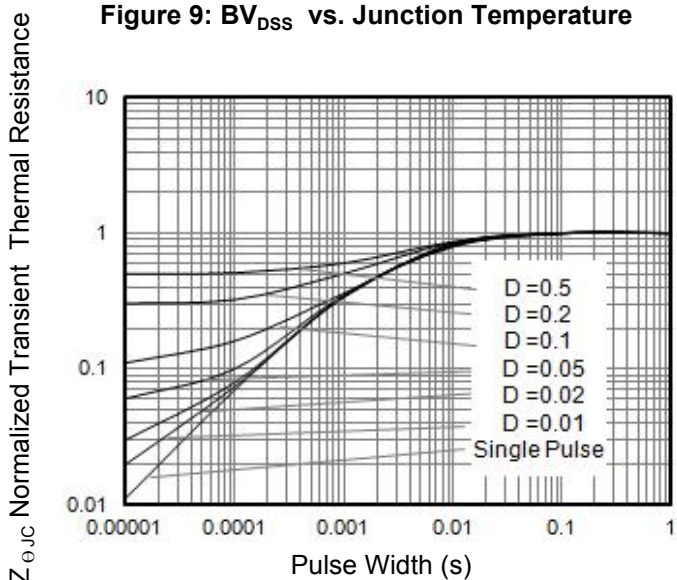


Figure 11: Normalized Transient Thermal Resistance

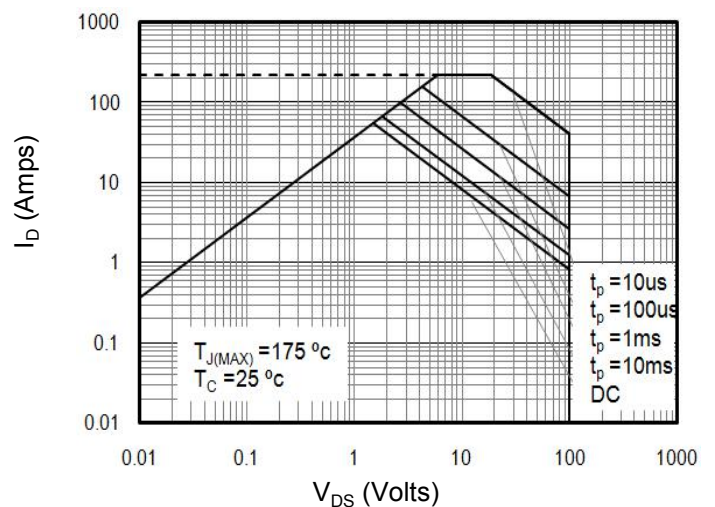


Figure 12: Safe Operating Area



Figure A: Gate Charge Test Circuit and Waveforms

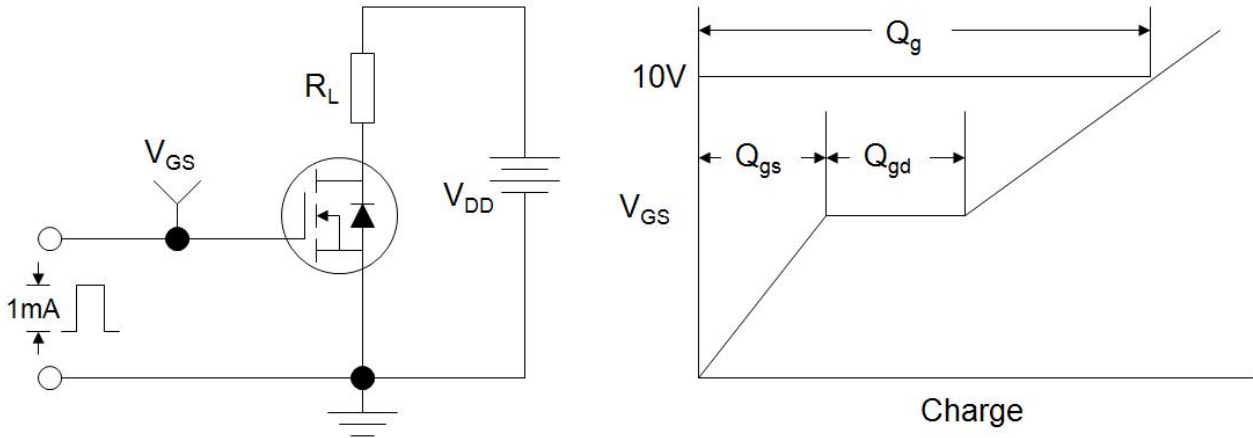


Figure B: Resistive Switching Test Circuit and Waveforms

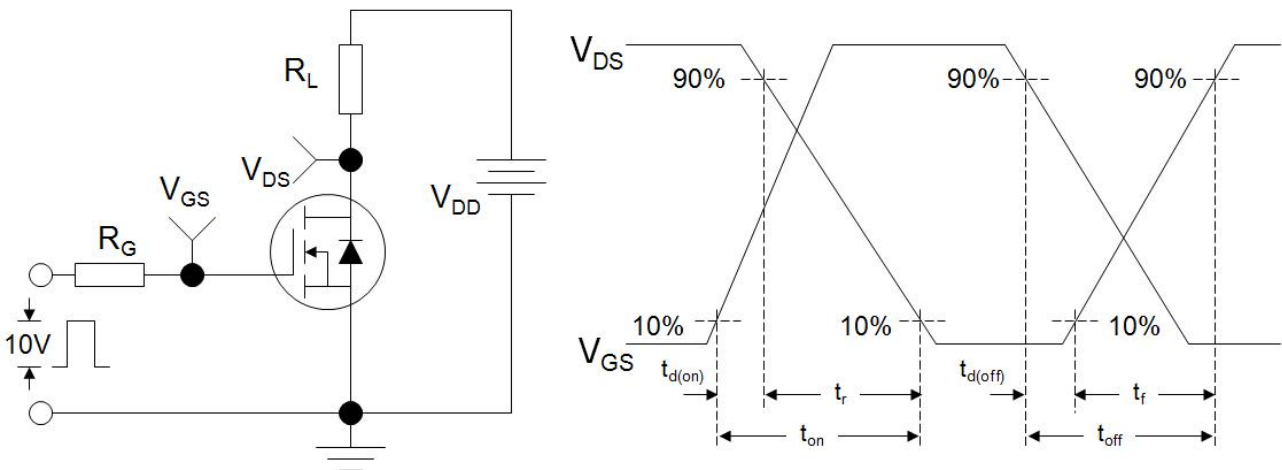
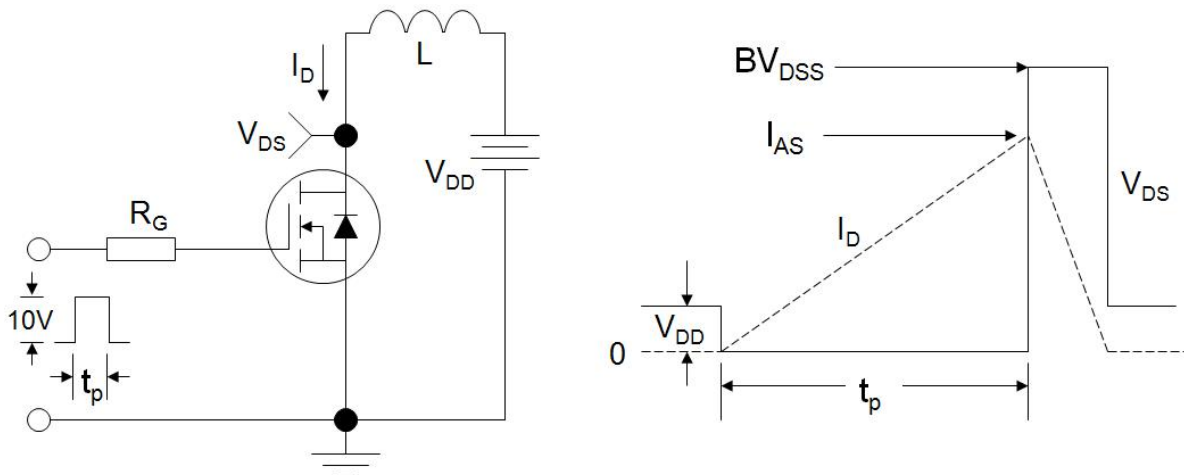
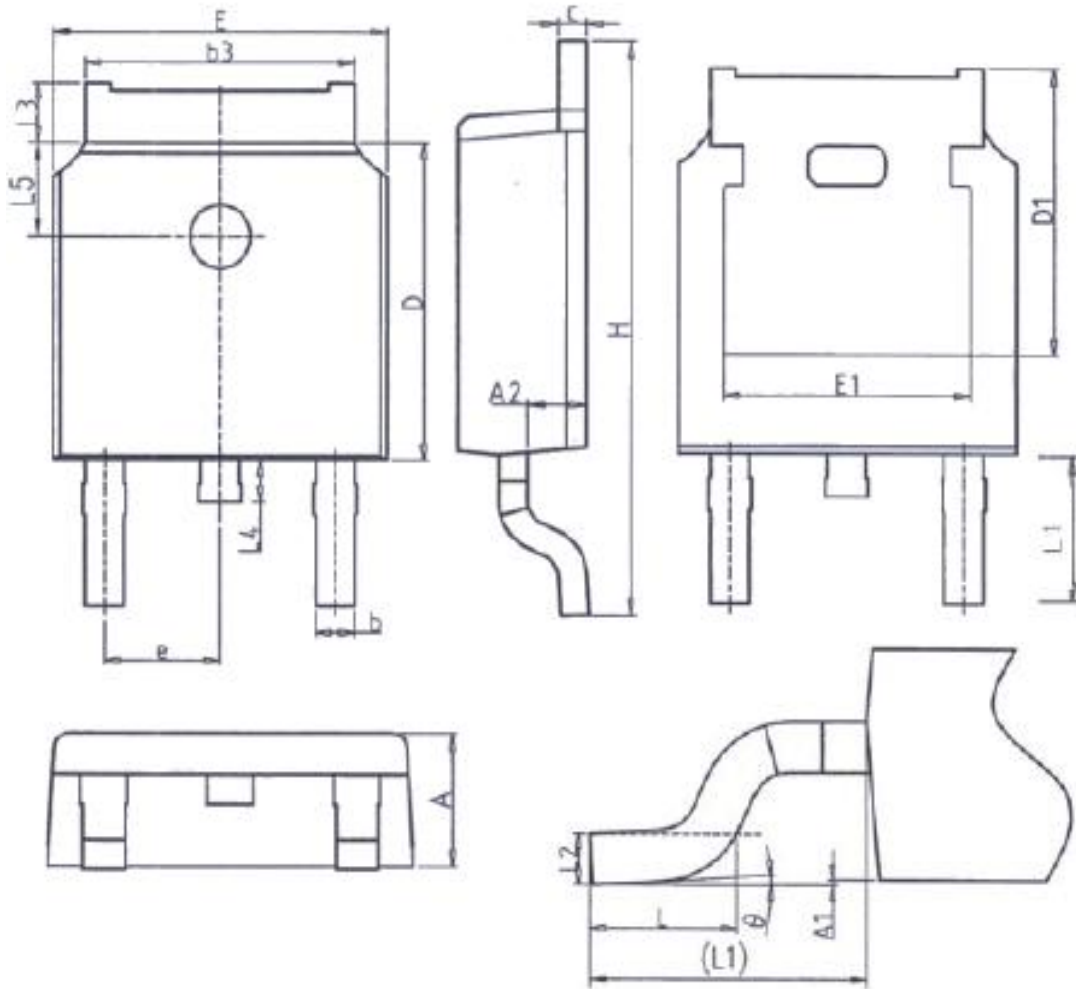


Figure C: Unclamped Inductive Switching (UIS) Test Circuit and Waveforms





## TO-252



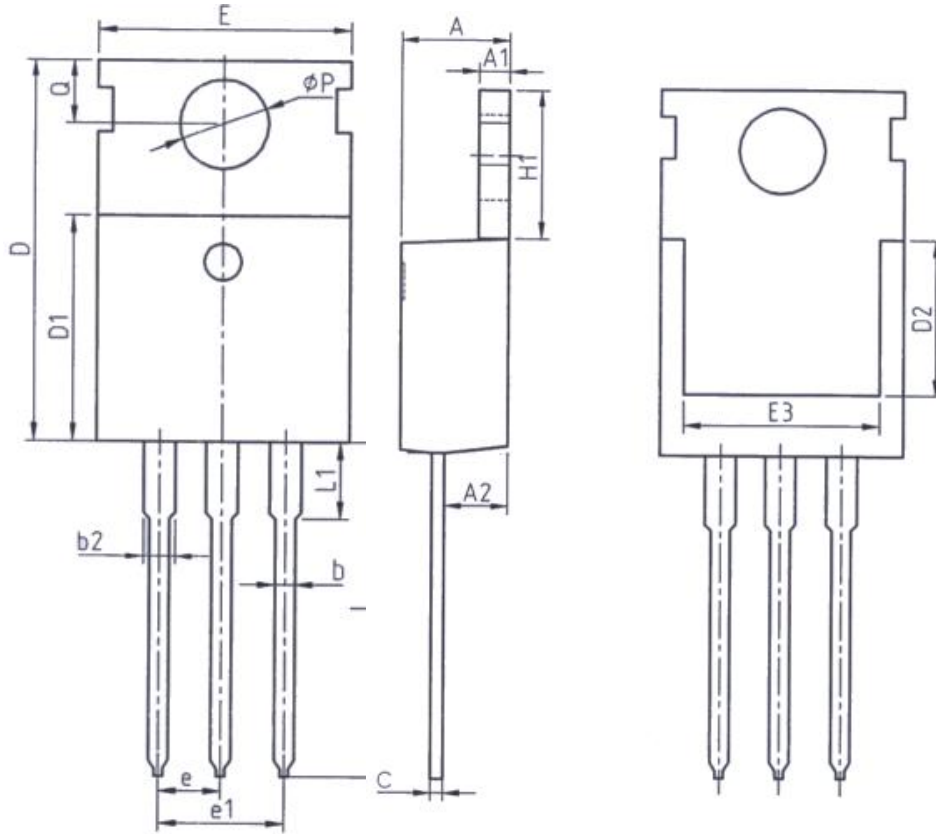
Unit: mm			
Symbol	Min	Nom	Max
A	2.20	2.30	2.38
A1	0.00	-	0.10
A2	0.90	1.01	1.10
b	0.72	-	0.85
b3	5.13	5.33	5.46
c	0.47	-	0.60
D	6.00	6.10	6.20
D1	5.25 REF		
E	6.50	6.60	6.70
E1	4.70	-	-

Unit: mm			
Symbol	Min	Nom	Max
e	2.286BSC		
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90REF		
L2	0.508BSC		
L3	0.90	-	1.25
L4	0.60	0.90	1.00
L5	1.8 REF		
θ	0°	-	8°





## TO-220

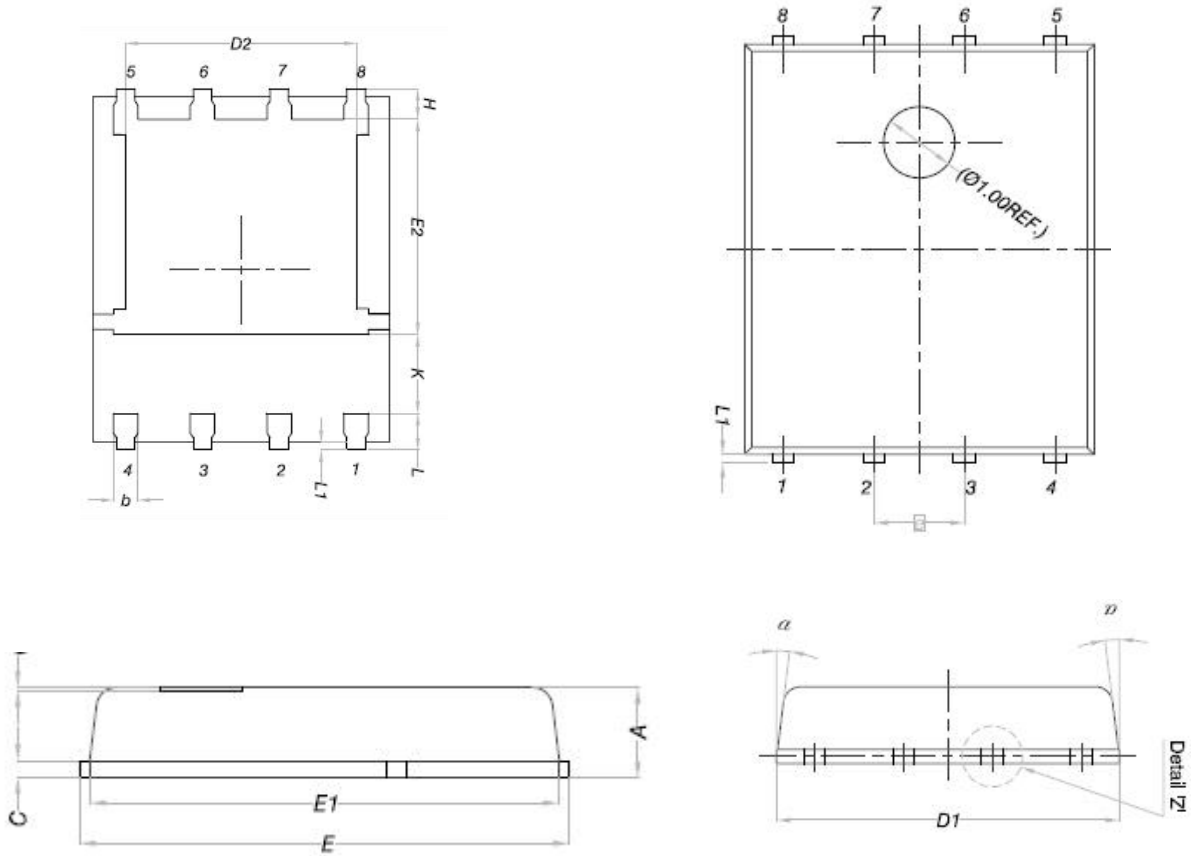


Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.25	1.45
A2	2.20	2.60
b	0.70	0.95
b2	1.17	1.47
c	0.40	0.65
D	15.10	16.10
D1	8.80	9.40
D2	5.50	-

Unit: mm		
Symbol	Min.	Max.
E	9.70	10.30
E3	7.00	-
e	2.54BSC	
e1	5.08BSC	
H1	6.25	6.85
L	12.75	13.80
L1	-	3.40
P	3.40	3.80
Q	2.60	3.00



## DFN5x6



DIM.	MILLIMETERS			DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.		MIN.	NOM.	MAX.
A	0.90	1.00	1.10	E	5.90	6.00	6.10
A1	0	-	0.05	E1	5.70	5.75	5.80
b	0.33	0.41	0.51	E2	3.38	3.58	3.78
C	0.20	0.25	0.30	e	1.27 BSC		
D1	4.80	4.90	5.00	H	0.41	0.51	0.61
D2	3.61	3.81	3.96	K	1.10	-	-
				L	0.51	0.61	0.71
				L1	0.06	0.13	0.20
				α	0°	-	12°





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